



### 6Gbps HDMI 2.0 1:2 Signal Duplicator

# Description

The DIODES PI3HDX612 active-drive Signal Duplicator solution is targeted for high-resolution video networks that are based on HDMI<sup>™</sup> 2.0 standards signal processing.

The PI3HDX612 is an active single-channel to two-channel Signal Duplicator. The device drives differential signals to multiple video display units. Depending on the mode select pin, the PI-3HDX612 provides controllable equalizer, flat gain and output swing linearity that can be manipulated through pin control or  $I^2C$  control.

The maximum HDMI<sup>™</sup> data rate of 6Gbps produces a 4K@60Hz resolution or 2K@144Hz, required for 4K HDTV, PC graphics products and other peripheral device. For PC graphics application, the device sits at the driver's side and fans out differential signals to multiple display units including PC LCD monitors, projectors, and TVs. The CTLE equalizers are implemented at the inputs of the ReDriver to reduce the ISI jitters and compensate channel loss. The PI3HDX612 ensures the transmittal of high bandwidth video streams from video sources to the end-display units.

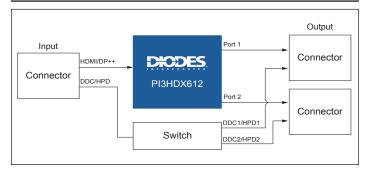
### Features

- 1-to-2 Active Signal Duplicator for 4-Lane HDMI 2.0 Operation •
- Data Rate Supports Up to 6Gbps and Supports 4K2K Pixel Resolution
- Quad-Level Equalizer Gain Value Selection Controlled By Pin Strap or I<sup>2</sup>C Mode Programming
- Quad-Level Flat Gain and Output Swing Linearity Selection Controlled By Pin Strap or I<sup>2</sup>C Mode Programming
- ESD Protection on I/O Pins: 2KV HBM
- Single Power Supply: 3.3V
- Temperature Support: -40°C to +70°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) •
- Halogen and Antimony Free. "Green" Device (Note 3) •
- For automotive applications requiring specific change • control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

- Packaging (Pb-free & Green):
  - 40-pin TQFN, 3 x 6 mm (0.4 mm pitch) (ZLD)

# Application Diagram



# Application(s)

- **Display Peripheral Boxes**
- Digital Signage Displays
- Multi-Screen Splicing

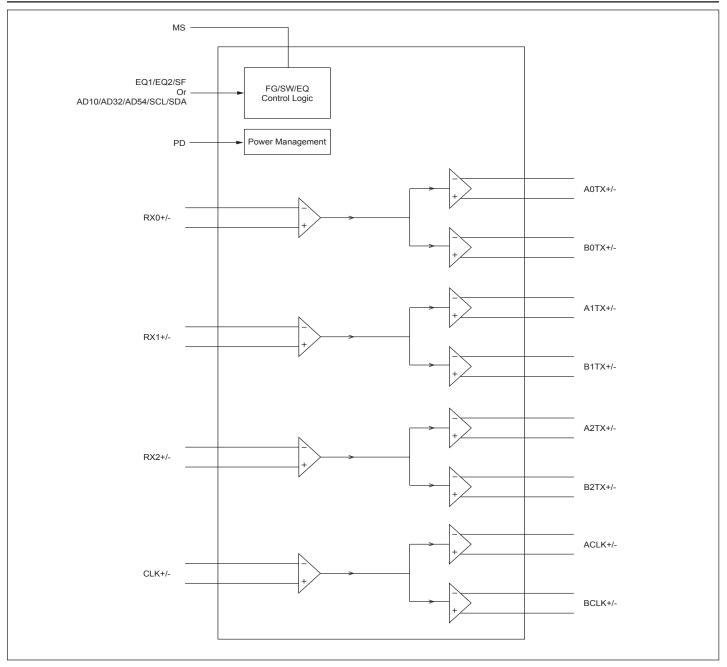
#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





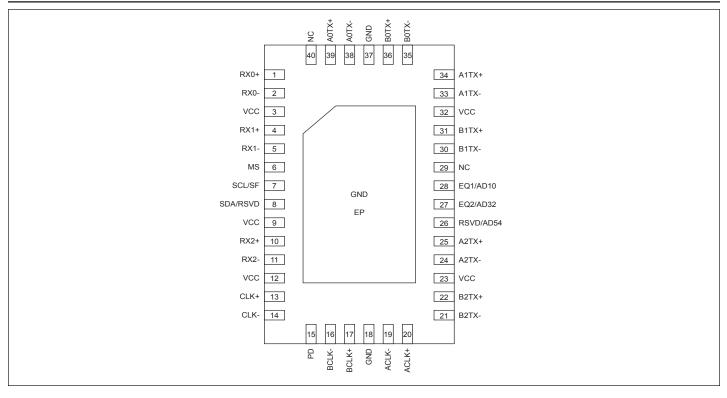
# **Block Diagram**







# **Pin Configuration (Top View)**







PI3HDX612

Pin Con	Pin Configuration (Top View)					
Pin #	Pin Name	Туре	Description			
Data Signa	ls					
1, 2	RX0+, RX0-	Ι	CML inputs for channel 0 with internal 50 $\Omega$ to VCC or HIZ.			
39, 38	A0TX+, A0TX-					
36, 35	В0ТХ+, В0ТХ-	0	CML outputs for channel A0/B0 with internal 50 $\Omega$ pullup or HIZ.			
4, 5	RX1+, RX1-	Ι	CML inputs for channel 1 with internal 50 $\Omega$ to VCC or HIZ.			
34, 33	A1TX+, A1TX-		CML sector to far abandal A1/D1 with internal 500 million on UUZ			
31, 30	B1TX+, B1TX-	0	CML outputs for channel A1/B1 with internal 50 $\Omega$ pullup or HIZ.			
10, 11	RX2+, RX2-	Ι	CML inputs for channel 2 with internal 50 $\Omega$ to VCC or HIZ.			
25, 24	A2TX+, A2TX-	O CML outputs for channel A2/B2 with internal 50 $\Omega$ pullup or HIZ.				
22, 21	B2TX+, B2TX-	0	CML outputs for channel A2/B2 with internal 5002 pullup or H1Z.			
13, 14	CLK+, CLK-	Ι	CML inputs for CLK channel with internal 50 $\Omega$ to VCC or HIZ.			
20, 19	ACLK+, ACLK-					
17, 16	BCLK+, BCLK-	0	CML outputs for CLKA/B channel with internal 50 $\Omega$ pullup or HIZ.			
Control Pi	18					
	EQ1, EQ2, RSVD	Ι	4-Level input pins with internal 100KΩ pullup and 200KΩ pulldown resistor. Sets the amount of equalizer boost on A & B channel. Reserved pin must tie to ground.			
28, 27, 26	AD10, AD32, AD54	Ι	4-Level input pins with internal 100K $\Omega$ pullup and 200K $\Omega$ pulldown resistor. Sets the I <sup>2</sup> C slave address.			
7, 8	SF, RSVD	Ι	4-Level input pins with internal 100KΩ pullup and 200KΩ pulldown resistor. Sets the output swing and flat gain level on A & B channel. Reserved pin must tie to ground.			
	SCL, SDA	I	I <sup>2</sup> C clock input and data input.			
6	MS	Ι	Input with internal 300KΩ pullup resistor. Pin mode enable pin Tie High = Pin mode Tie Low = Register access I <sup>2</sup> C slave mode			
29, 40	NC		Not Connected			
15	PD	Ι	Input with internal 300K $\Omega$ pullup resistor. When High, the device is put in Power Down Mode. When Low, the device is Enable and in Normal Operation.			
Power Pins						
3, 9, 12, 23,	32 VCC	PWR	3.3V supply voltage.			
18, 37, EP	GND	PWR	Exposed pad. Supply ground.			
	L	1				





# **Functional Description & Circuit Block Description**

#### **Power Enable Function**

When PD is set to high, the IC goes into power down mode, both input and output termination set to high impedance. Individual channel enabling is done through the I<sup>2</sup>C register programming.

# EQ Setting in Pin Mode and I<sup>2</sup>C Mode

#### Table 1. EQ1/EQ2 are the Selection Pins for the Equalization Setting

Equalizer Setting (dB)						
EQ1	EQ2	I <sup>2</sup> C EQ<2:0>	@1.25GHz	@1.7GHz	@3GHz	
0	0	000	0.5	0.9	2.5	
0	F	001	0.6	1.1	3.1	
R	0	010	2.0	2.5	4.1	
R	F	011	2.2	2.9	4.9	
F	0	100	3.1	3.8	5.9	
F	F	101	3.4	4.2	6.7	
1	0	110	4.3	5.1	7.7	
1	F	111	4.8	5.8	8.9	

### Swing and Flat Gain Setting

### Table 2. Swing and Flat Gain Setting for SF

SF	Swing (mVp-p)	Flat Gain (dB)	
0	1000	-3.5	
R	1000	-0.5	
F	1200	-3.5	
1	1200	-0.5	

### Table 3. Swing Settings in I<sup>2</sup>C Mode

SW1	SW0	Swing (mVp-p)
0	0	800
0	1	1000 (default)
1	0	1100
1	1	1200

### Table 4. Flat Gain Setting in I<sup>2</sup>C Mode

FG1	FG0	Flat Gain (dB)	
0	0	-3.5	
0	1	-2	
1	0	-0.5 (default)	
1	1	1	





### Table 5. I<sup>2</sup>C Address Settings

AD54	AD5	AD4
0	0	0
R	0	1
F	1	0
1	1	1

AD32	AD3	AD2
0	0	0
R	0	1
F	1	0
1	1	1

AD10	AD1	AD0
0	0	0
R	0	1
F	1	0
1	1	1





# I<sup>2</sup>C Programming

Address Assig	gnment						
A6	A5	A4	A3	A2	A1	A0	R/W
1	AD5	AD4	AD3	AD2	AD1	AD0	1=R, 0=W

BYTE 0							
Bit	Туре	Power up Condition	Field	Control Affected	Comment		
7	R	0		Reserved			
6	R	0		Reserved			
5	R	1		Reserved			
4	R	1		Reserved			
3	R	0					
2	R	0					
1	R	0		Rev. $ID = 0x0$			
0	R	0					

# **BVTF 1**

Bit	Туре	Power up Condition	Field	Control Affected	Comment	
7	R	0		Reserved		
6	R	0		Reserved		
5	R	0		Reserved		
4	R	0		Reserved		
3	R	0		Reserved	Reserved	
2	R	0		Reserved		
1	R	0		Reserved		
0	R	0		Reserved		





BYTE 2							
Bit	Туре	Power up Condition	Field	Control Affected	Comment		
7	R/W	0		Channel 3 Power down			
6	R/W	0		Channel 2 Power down	1 December		
5	R/W	0		Channel 1 Power down	1 = Power down		
4	R/W	0		Channel 0 Power down			
3	R/W	1		Reserved			
2	R/W	1		Reserved			
1	R/W	0		Reserved			
0	R/W	1		Reserved			

### BYTE 3

		ï	1		
Bit	Туре	Power up Condition	Field	Control Affected	Comment
7	R/W	0		Reserved	
6	R/W	0		EQ2	E
5	R/W	0		EQ1	Equalizer
4	R/W	0		EQ0	
3	R/W	1	Channel 0 configuration	FG1	
2	R/W	0		FG0	Flat Galli
1	R/W	0	-	SW1	Couring a
0	R/W	1		SW0	Swing

## BYTE 4

Bit	Туре	Power up Condition	Field	<b>Control Affected</b>	Comment
7	R/W	0		Reserved	
6	R/W	0		EQ2	F 1:
5	R/W	0		EQ1	Equalizer
4	R/W	0		EQ0	
3	R/W	1	Channel 1 configuration	FG1	
2	R/W	0		FG0	Flat Gain
1	R/W	0	-	SW1	Consistent of
0	R/W	1		SW0	Swing





BYTE 5							
Bit	Туре	Power up Condition	Field	Control Affected	Comment		
7	R/W	0		Reserved			
6	R/W	0		EQ2	E 1:		
5	R/W	0	-	EQ1	Equalizer		
4	R/W	0		EQ0			
3	R/W	1	Channel 2 configuration	FG1			
2	R/W	0		FG0	Flat Gain		
1	R/W	0		SW1	0		
0	R/W	1		SW0	Swing		

BYTE 6								
Bit	Туре	Power up Condition	Field	Control Affected	Comment			
7	R/W	0		Reserved				
6	R/W	0		EQ2				
5	R/W	0		EQ1	Equalizer			
4	R/W	0		EQ0				
3	R/W	1	Channel 3 configuration	FG1				
2	R/W	0		FG0	Flat Gain			
1	R/W	0		SW1	0			
0	R/W	1		SW0	Swing			



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# I<sup>2</sup>C Operation

The integrated I<sup>2</sup>C interface operates as slave device when 'MS" set to logic low. Standard mode (100Kbps) is supported with 7-bit addressing. The data byte format is 8-bit bytes and supports the format of indexing to be compatible with other bus devices. In the Slave mode (MS = LOW), the device supports Read/Write. The bytes must be accessed in sequential order from the lowest to the highest byte with the ability to stop after any complete byte has been transferred.

Address bits A5 to A0 are configurable by hardware strap pin to support multiple chips environment.

# **Transferring Data**

Every byte put on the SDA line must be 8-bits long. Each byte must be followed by an acknowledge bit. Data is transferred with the most significant bit (MSB) first (see the I<sup>2</sup>C Data Transfer diagram). The device never holds the clock line SCL to low to force the master into a wait state.

# Acknowledge

Data transfer with acknowledge is required from the master. When the master releases the SDA line (HIGH) during the acknowledge clock pulse, the device pulls down the SDA line during the acknowledge clock pulse, so it remains stable LOW during the HIGH period of this clock pulse as indicated in the  $I^2C$  Data Transfer diagram. The device generates an acknowledge after each byte has been received.

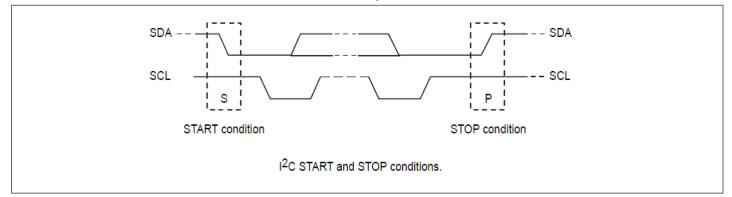
# Data Transfer

A data transfer cycle begins with the master issuing a start bit. After recognizing a start bit, the device watches the next byte of information for a match with its address setting. When a match is found it responds with a read or write of data on the following clocks. Each byte must be followed by an acknowledge bit except for the last byte of a read cycle, which ends with a stop bit. For a write cycle, the first data byte following the address byte is an index byte that is used by the device. Data is transferred with the most significant bit (MSB) first.

# I<sup>2</sup>C Data Transfer

### Start & Stop Conditions

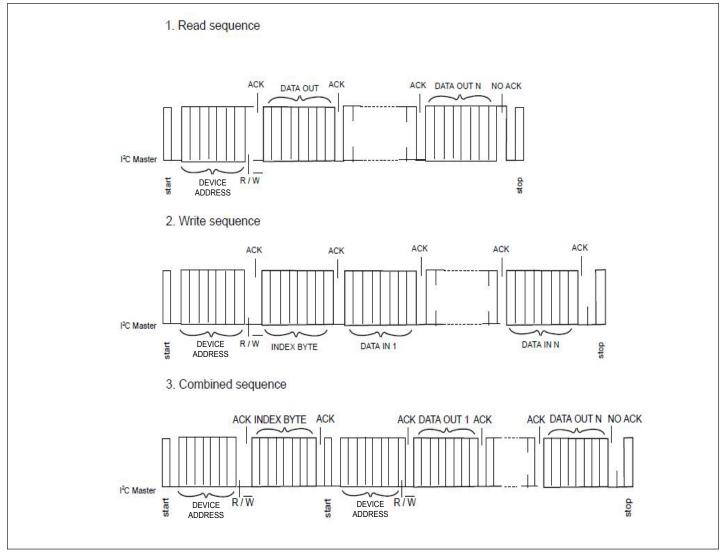
A HIGH-to-LOW transition on the SDA line while SCL is HIGH indicates a START condition. A LOW-to-HIGH transition on the SDA line while SCL is HIGH defines a STOP condition, as shown in the figure below.







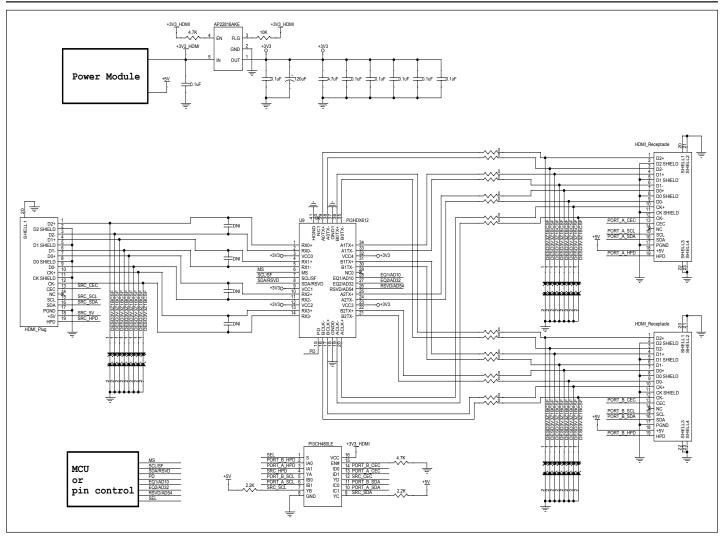
# I<sup>2</sup>C Data Transfer







# **Application Schematics**







# **Maximum Ratings**

(Above which useful life may be impaired. For user guidelines, not tested.)	
Storage Temperature -65°C to +150°C   Supply Voltage to Ground Potential -0.5V to +3.8V   DC SIG Voltage -0.5V to V <sub>CC</sub> +0.5V   ESD, HBM. -2kV to +2kV	Note: Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification s not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

# **Thermal Information**

Symbol	Parameter	40-pin TQFN (ZLD) Package	Units
Theta JA	Junction to Ambient Thermal Resistance	17.91	°C/W

# **Rommended Operating Condidtions**

Symbol	Parameter	Min.	Тур.	Max.	Units
VCC	Supply Voltage	3.0	3.3	3.6	V
ТА	Ambient Temperature	-40		+70	°C

# **Electrical Characteristics - LVCMOS I/O DC Specifications**

$V_{CC} = 3.3 \pm 0.3$ V, $T_A = -40$ °C to 70°C

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V <sub>IH</sub>	DC Input Logic High		0.44 VCC		VCC + 0.3	V
V <sub>IL</sub>	DC Input Logic Low		-0.3		0.1 VCC	V
4-Level Cont	rol Pins					
V <sub>IH</sub>	DC Input Logic "High"		0.92×VCC	VCC		V
V <sub>IF</sub>	DC Input Logic "Float"		0.59×VCC	0.67×VCC	0.75×VCC	V
V <sub>IR</sub>	DC Input Logic "With Rext to GND"		0.25×VCC	0.33×VCC	0.41×VCC	V
V <sub>IL</sub>	DC Input Logic "Low"			GND	0.08×VCC	V
I <sub>IH</sub>	Input High Current				50	μΑ
I <sub>IL</sub>	Input Low Current		-50			μΑ
Rext	External Resistance Connects to GND (±5%)		64.6	68	71.4	kΩ





# Electrical Characteristics - SDA and SCL I/O for $I^2C$ -bus

 $V_{CC}$  = 3.3 ± 0.3V,  $T_A$  = -40°C to 70°C

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V <sub>IH</sub>	DC Input Logic High		$V_{\rm CC}/2+0.7$		V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	DC Input Logic Low		-0.3		V <sub>CC</sub> /2 - 0.7	V
V <sub>OL</sub>	DC Output Logic Low	$I_{OL} = 3mA$			0.4	V
V <sub>hys</sub>	Hysteresis of Schmitt Trigger Input		0.8			V
t <sub>of</sub>	Output Fall Time from $V_{IHmin}$ to $V_{ILmax}$ with Bus Capacitance 10-400pF				250	ns
f <sub>SCL</sub>	SCL Clock Frequency				100	kHz

# Electrical Characteristics - High Speed I/O AC/DC Specifications

 $V_{CC}$  = 3.3  $\pm$  0.3V,  $T_A$  = -40°C to 70°C

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
C <sub>RX</sub>	RX AC Coupling Capacitance			220		nF
0	I (D) I	10MHz to 3GHz Differential		-21		ID
S <sub>11</sub>	Input Return Loss	1GHz to 3GHz Common Mode		-7		dB
C	Outrast Datase Land	10MHz to 3GHz Differential		-20		at
S <sub>22</sub>	Output Return Loss	1GHz to 3GHz Common Mode		-9		dB
D	DC Single-Ended Input Impedance			50		
R <sub>IN</sub>	DC Differential Input Impedance			100		Ω
R <sub>OUT</sub>	DC Single-Ended Output Impedance			50		Ω
JOUT	DC Differential Output Impedance			100		
Z <sub>RX-HIZ</sub>	DC Input CM Input Impedance During Reset or Power Down			78		kΩ
V <sub>RX-DIFF-PP</sub>	Differential Input Peak-to-Peak Voltage	Operational			1.2	Vppd
V <sub>RX_CM</sub>	Input Source Common-Mode Noise	DC – 200MHz			150	mVpp
P <sub>active</sub>	Supply Power @ Active Mode, with Signal				1656	mW
I <sub>active</sub>	Supply Current @ Active Mode, with Signal	PD = 0			460	mA
I <sub>standby</sub>	Supply Current @ Standby Mode	PD = 1			110	uA
t <sub>pd</sub>	Latency	From Input to Output		0.5		ns





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Gp	Peaking Gain (Compensation at 3GHz, Relative to 100MHz,	EQ<2:0> = 111 EQ<2:0> = 000		8.9 2.5		dB
	100mVp-p Sine Wave Input)	Variation Around Typical	-3		+3	dB
G <sub>F</sub>	Flat Gain (100MHz)	SF = R/1 SF = 0/F		-0.5 -3.5		dB
1		Variation Around Typical	-3		+3	dB
V <sub>1dB_100M</sub>	-1dB Compression Point of Output Swing (at 100MHz)	SF = 1, EQ<2:0> = 111 SF = R, EQ<2:0> = 111		1200 1100		mVppd
V <sub>1dB_3G</sub>	-1dB Compression Point of Output Swing (at 3GHz)	SF = 1, EQ<2:0> = 111 SF = R, EQ<2:0> = 111		1100 900		mVppd
V <sub>Coup</sub>	Channel Isolation	100MHz to 3GHz, at EQ = 000 Figure 1 (Note 1)		-50		dB
17	Input-Referred Noise	100MHz to 3GHz, SF = 1, EQ<2:0> = 000, Figure 2		0.8		
V <sub>noise_input</sub>		100MHz to 3GHz, SF = 1, EQ<2:0> = 111, Figure 2		0.5		mV <sub>RMS</sub>
17		100MHz to 3GHz, SF = 1, EQ<2:0> = 000, Figure 2		0.7		
V <sub>noise_output</sub>	Output-Referred Noise <sup>(2)</sup>	100MHz to 3GHz, SF = 1, EQ<2:0> = 111, Figure 2		1.0		mV <sub>RMS</sub>

Note:

1. Measured using a vector-network analyzer (VNA) with -30dBm power level applied to the adj cent input. The VNA detects the signal at the output of the victim channel. All other inputs and outputs are terminated with  $50\Omega$ .

2. Guaranteed by design and characterization.





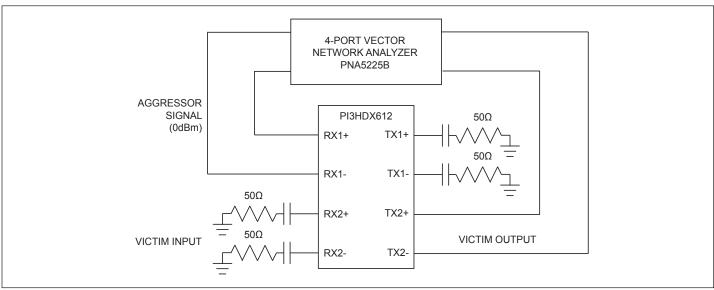


Figure 1. Channel-Isolation Test Configuration

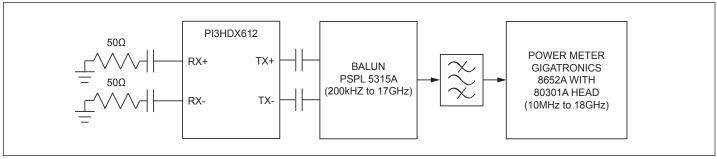


Figure 2. Noise Test Configuration

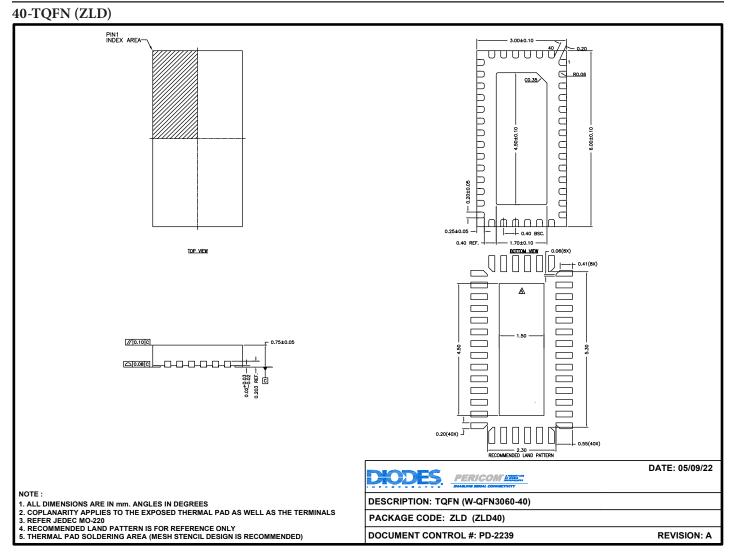
# **Part Marking**

PI3HDX6 12ZLDE
$\circ$ YYWWX $\overline{X}$
YY: Year WW: Workweek
1st X: Assembly Code 2nd X: Fab Code





## **Packaging Mechanical**



For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

## **Ordering Information**

Ordering Number	Package Code	Package Description
PI3HDX612ZLDEX	ZLD	TQFN (W-QFN3060-40)

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm

antimony compounds.

4. E = Pb-free and Green

5. X suffix = Tape/Reel





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